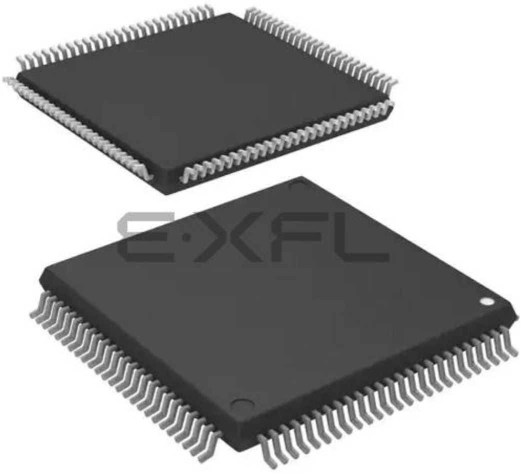

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

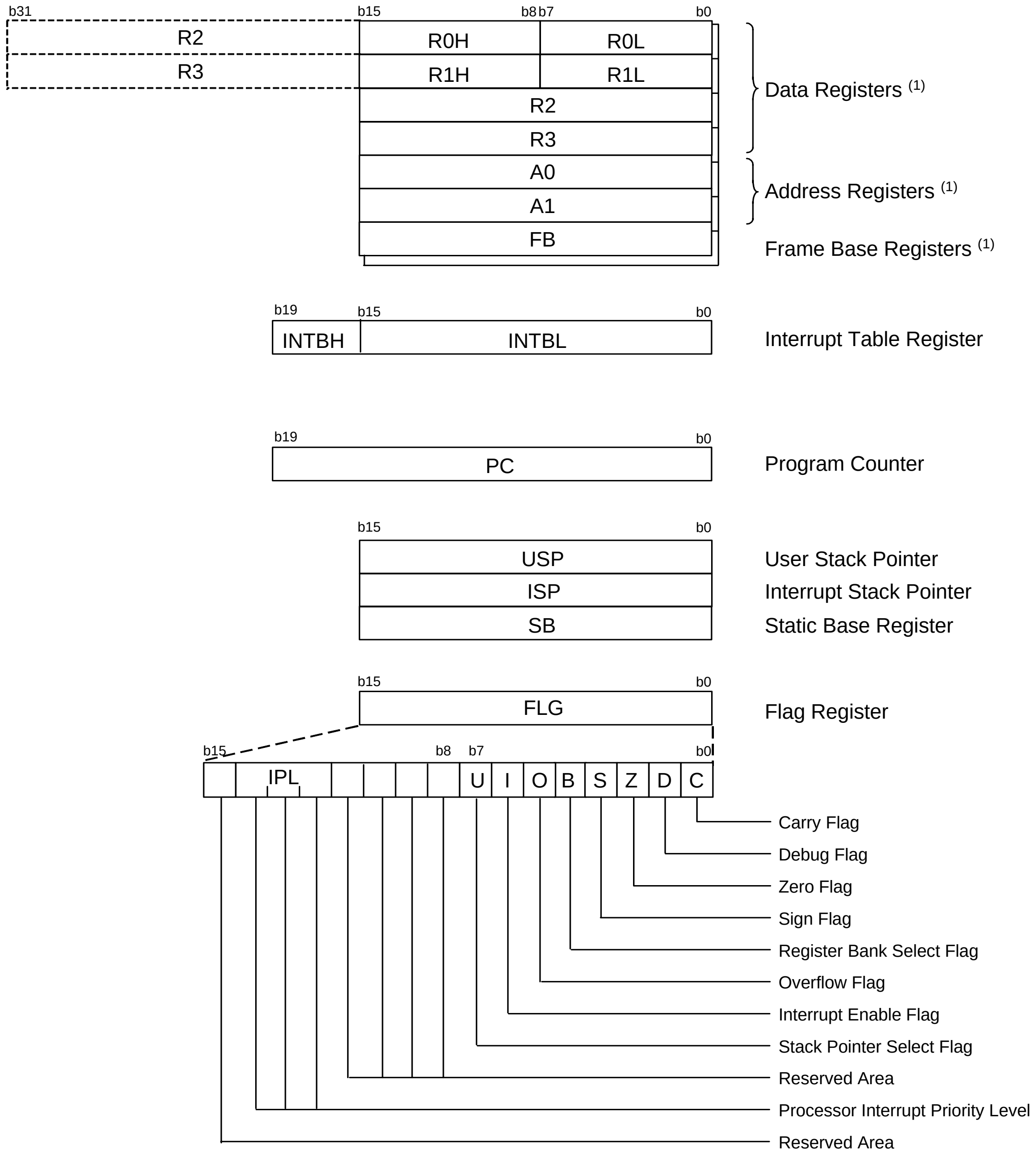
Details	
Product Status	Not For New Designs
Core Processor	M16C/60
Core Size	16-Bit
Speed	24MHz
Connectivity	I²C, IEBus, UART/USART
Peripherals	DMA, WDT
Number of I/O	85
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 26x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LFQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/m30624fgpgp-u5c

Table 1.15 Pin Characteristics for 80-Pin Package (1)

Pin No.	Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
1		P9_5			CLK4	ANEX0	
2		P9_4		TB4IN		DA1	
3		P9_3		TB3IN		DA0	
4		P9_2		TB2IN	SOUT3		
5		P9_0		TB0IN	CLK3		
6	CNVSS (BYTE)						
7	XCIN	P8_7					
8	XCOUT	P8_6					
9	$\overline{\mathrm{RESET}}$						
10	XOUT						
11	VSS						
12	XIN						
13	VCC1						
14		P8_5	$\overline{\mathrm{NMI}}$				
15		P8_4	$\overline{\mathrm{INT2}}$	ZP			
16		P8_3	$\overline{\mathrm{INT1}}$				
17		P8_2	$\overline{\mathrm{INT0}}$				
18		P8_1		TA4IN			
19		P8_0		TA4OUT			
20		P7_7		TA3IN			
21		P7_6		TA3OUT			
22		P7_1		TA0IN/TB5IN	RXD2/SCL2		
23		P7_0		TA0OUT	TXD2/SDA2		
24		P6_7			TXD1/SDA1		
25		P6_6			RXD1/SCL1		
26		P6_5			CLK1		
27		P6_4			$\overline{\mathrm{CTS1}}$/$\overline{\mathrm{RTS1}}$/$\overline{\mathrm{CTS0}}$/CLKS1		
28		P6_3			TXD0/SDA0		
29		P6_2			RXD0/SCL0		
30		P6_1			CLK0		
31		P6_0			$\overline{\mathrm{CTS0}}$/$\overline{\mathrm{RTS0}}$		
32		P5_7					CLKOUT
33		P5_6					
34		P5_5					
35		P5_4					
36		P5_3					
37		P5_2					
38		P5_1					
39		P5_0					
40		P4_3					
41		P4_2					
42		P4_1					
43		P4_0					
44		P3_7					
45		P3_6					
46		P3_5					
47		P3_4					
48		P3_3					
49		P3_2					
50		P3_1					

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU registers. The CPU has 13 registers. Of these, R0, R1, R2, R3, A0, A1 and FB comprise a register bank. There are two register banks.



NOTES:
1. These registers comprise a register bank. There are two register banks.

Figure 2.1 Central Processing Unit Register

2.1 Data Registers (R0, R1, R2 and R3)

The R0 register consists of 16 bits, and is used mainly for transfers and arithmetic/logic operations. R1 to R3 are the same as R0.

The R0 register can be separated between high (R0H) and low (R0L) for use as two 8-bit data registers.

R1H and R1L are the same as R0H and R0L. Conversely, R2 and R0 can be combined for use as a 32-bit data register (R2R0). R3R1 is the same as R2R0.

4. Special Function Register (SFR)

SFR(Special Function Register) is the control register of peripheral functions. Tables 4.1 to 4.6 list the SFR information.

Table 4.1 SFR Information (1) (1)

Address	Register	Symbol	After Reset
0000h			
0001h			
0002h			
0003h			
0004h	Processor Mode Register 0 (2)	PM0	00000000b(CNVSS pin is “L”) 00000011b(CNVSS pin is “H”)
0005h	Processor Mode Register 1	PM1	00001000b
0006h	System Clock Control Register 0	CM0	01001000b
0007h	System Clock Control Register 1	CM1	00100000b
0008h	Chip Select Control Register (6)	CSR	00000001b
0009h	Address Match Interrupt Enable Register	AIER	XXXXXX00b
000Ah	Protect Register	PRCR	XX000000b
000Bh	Data Bank Register (6)	DBR	00h
000Ch	Oscillation Stop Detection Register (3)	CM2	0X000000b
000Dh			
000Eh	Watchdog Timer Start Register	WDTS	XXh
000Fh	Watchdog Timer Control Register	WDC	00XXXXXXb (4)
0010h	Address Match Interrupt Register 0	RMAD0	00h
0011h			00h
0012h			X0h
0013h			
0014h	Address Match Interrupt Register 1	RMAD1	00h
0015h			00h
0016h			X0h
0017h			
0018h			
0019h	Voltage Detection Register 1 (5, 6)	VCR1	00001000b
001Ah	Voltage Detection Register 2 (5, 6)	VCR2	00h
001Bh	Chip Select Expansion Control Register (6)	CSE	00h
001Ch	PLL Control Register 0	PLC0	0001X010b
001Dh			
001Eh	Processor Mode Register 2	PM2	XXX00000b
001Fh	Low Voltage Detection Interrupt Register (6)	D4INT	00h
0020h	DMA0 Source Pointer	SAR0	XXh
0021h			XXh
0022h			XXh
0023h			
0024h	DMA0 Destination Pointer	DAR0	XXh
0025h			XXh
0026h			XXh
0027h			
0028h	DMA0 Transfer Counter	TCR0	XXh
0029h			XXh
002Ah			
002Bh			
002Ch	DMA0 Control Register	DM0CON	00000X00b
002Dh			
002Eh			
002Fh			
0030h	DMA1 Source Pointer	SAR1	XXh
0031h			XXh
0032h			XXh
0033h			
0034h	DMA1 Destination Pointer	DAR1	XXh
0035h			XXh
0036h			XXh
0037h			
0038h	DMA1 Transfer Counter	TCR1	XXh
0039h			XXh
003Ah			
003Bh			
003Ch	DMA1 Control Register	DM1CON	00000X00b
003Dh			
003Eh			
003Fh			

NOTES:

1. The blank areas are reserved and cannot be accessed by users.
2. The PM00 and PM01 bits do not change at software reset, watchdog timer reset and oscillation stop detection reset.
3. The CM20, CM21, and CM27 bits do not change at oscillation stop detection reset.
4. The WDC5 bit is “0” (cold start) immediately after power-on. I t can only be set to “1” in a program.
5. This register does not change at software reset, watchdog timer reset and oscillation stop detection reset.
6. This register in M16C/62PT cannot be used.

X : Nothing is mapped to this bit

Table 4.4 SFR Information (4) (1)

Address	Register	Symbol	After Reset
0340h	Timer B3, 4, 5 Count Start Flag	TBSR	000XXXXXb
0341h			
0342h	Timer A1-1 Register	TA11	XXh
0343h			XXh
0344h	Timer A2-1 Register	TA21	XXh
0345h			XXh
0346h	Timer A4-1 Register	TA41	XXh
0347h			XXh
0348h	Three-Phase PWM Control Register 0	INVC0	00h
0349h	Three-Phase PWM Control Register 1	INVC1	00h
034Ah	Three-Phase Output Buffer Register 0	IDB0	00h
034Bh	Three-Phase Output Buffer Register 1	IDB1	00h
034Ch	Dead Time Timer	DTT	XXh
034Dh	Timer B2 Interrupt Occurrence Frequency Set Counter	ICTB2	XXh
034Eh			
034Fh			
0350h	Timer B3 Register	TB3	XXh
0351h			XXh
0352h	Timer B4 Register	TB4	XXh
0353h			XXh
0354h	Timer B5 Register	TB5	XXh
0355h			XXh
0356h			
0357h			
0358h			
0359h			
035Ah			
035Bh	Timer B3 Mode Register	TB3MR	00XX0000b
035Ch	Timer B4 Mode Register	TB4MR	00XX0000b
035Dh	Timer B5 Mode Register	TB5MR	00XX0000b
035Eh	Interrupt Factor Select Register 2	IFSR2A	00XXXXXXb
035Fh	Interrupt Factor Select Register	IFSR	00h
0360h	SI/O3 Transmit/Receive Register	S3TRR	XXh
0361h			
0362h	SI/O3 Control Register	S3C	01000000b
0363h	SI/O3 Bit Rate Generator	S3BRG	XXh
0364h	SI/O4 Transmit/Receive Register	S4TRR	XXh
0365h			
0366h	SI/O4 Control Register	S4C	01000000b
0367h	SI/O4 Bit Rate Generator	S4BRG	XXh
0368h			
0369h			
036Ah			
036Bh			
036Ch	UART0 Special Mode Register 4	U0SMR4	00h
036Dh	UART0 Special Mode Register 3	U0SMR3	000X0X0Xb
036Eh	UART0 Special Mode Register 2	U0SMR2	X0000000b
036Fh	UART0 Special Mode Register	U0SMR	X0000000b
0370h	UART1 Special Mode Register 4	U1SMR4	00h
0371h	UART1 Special Mode Register 3	U1SMR3	000X0X0Xb
0372h	UART1 Special Mode Register 2	U1SMR2	X0000000b
0373h	UART1 Special Mode Register	U1SMR	X0000000b
0374h	UART2 Special Mode Register 4	U2SMR4	00h
0375h	UART2 Special Mode Register 3	U2SMR3	000X0X0Xb
0376h	UART2 Special Mode Register 2	U2SMR2	X0000000b
0377h	UART2 Special Mode Register	U2SMR	X0000000b
0378h	UART2 Transmit/Receive Mode Register	U2MR	00h
0379h	UART2 Bit Rate Generator	U2BRG	XXh
037Ah 037Bh	UART2 Transmit Buffer Register	U2TB	XXh XXh
037Ch	UART2 Transmit/Receive Control Register 0	U2C0	00001000b
037Dh	UART2 Transmit/Receive Control Register 1	U2C1	00000010b
037Eh 037Fh	UART2 Receive Buffer Register	U2RB	XXh XXh

NOTES:

1. The blank areas are reserved and cannot be accessed by users.

X : Nothing is mapped to this bit

Table 5.5 D/A Conversion Characteristics (1)

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
–	Resolution				8	Bits
–	Absolute Accuracy				1.0	%
t_{SU}	Setup Time				3	μs
R_O	Output Resistance		4	10	20	kΩ
I_{VREF}	Reference Power Supply Input Current	(NOTE 2)			1.5	mA

NOTES:

1. Referenced to $V_{CC1}=V_{REF}=3.3$ to 5.5V, $V_{SS}=AV_{SS}=0V$ at T_{opr} = −20 to 85°C / −40 to 85°C unless otherwise specified.
2. This applies when using one D/A converter, with the D/A register for the unused D/A converter set to “00h”. The resistor ladder of the A/D converter is not included. Also, when D/A register contents are not “00h”, the I_{VREF} will flow even if Vref id disconnected by the A/D control register.

Table 5.6 Flash Memory Version Electrical Characteristics (1) for 100 cycle products (D3, D5, U3, U5)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3)		100			cycle
–	Word Program Time (V_{CC1}=5.0V)			25	200	µs
–	Lock Bit Program Time			25	200	µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block		0.3	4	s
–		8-Kbyte block		0.3	4	s
–		32-Kbyte block		0.5	4	s
–		64-Kbyte block		0.8	4	s
–	Erase All Unlocked Blocks Time (2)				4×n	s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		10			year

Table 5.7 Flash Memory Version Electrical Characteristics (6) for 10,000 cycle products (D7, D9, U7, U9) (Block A and Block 1 (7))

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3, 8, 9)		10,000 (4)			cycle
–	Word Program Time (V_{CC1}=5.0V)			25		µs
–	Lock Bit Program Time			25		µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block		0.3		s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		10			year

NOTES:

1. Referenced to V_{CC1}=4.5 to 5.5V, 3.0 to 3.6V at Topr = 0 to 60 °C (D3, D5, U3, U5) unless otherwise specified.
2. n denotes the number of block erases.
3. Program and Erase Endurance refers to the number of times a block erase can be performed.
   If the program and erase endurance is n (n=100, 1,000, or 10,000), each block can be erased n times.
   For example, if a 4 Kbytes block A is erased after writing 1 word data 2,048 times, each to a different address, this counts as one program and erase endurance. Data cannot be written to the same address more than once without erasing the block. (Rewrite prohibited)
4. Maximum number of E/W cycles for which operation is guaranteed.
5. Topr = -40 to 85 °C (D3, D7, U3, U7) / -20 to 85 °C (D5, D9, U5, U9).
6. Referenced to V_{CC1} = 4.5 to 5.5V, 3.0 to 3.6V at T_{opr} = -40 to 85 °C (D7, U7) / -20 to 85 °C (D9, U9) unless otherwise specified.
7. Table 5.7 applies for block A or block 1 program and erase endurance > 1,000. Otherwise, use Table 5.6.
8. To reduce the number of program and erase endurance when working with systems requiring numerous rewrites, write to unused word addresses within the block instead of rewrite. Erase block only after all possible addresses are used. For example, an 8-word program can be written 256 times maximum before erase becomes necessary.
   Maintaining an equal number of erasure between block A and block 1 will also improve efficiency. It is important to track the total number of times erasure is used.
9. Should erase error occur during block erase, attempt to execute clear status register command, then block erase command at least three times until erase error disappears.
10. Set the PM17 bit in the PM1 register to "1" (wait state) when executing more than 100 times rewrites (D7, D9, U7 and U9).
11. Customers desiring E/W failure rate information should contact their Renesas technical support representative.

Table 5.8 Flash Memory Version Program / Erase Voltage and Read Operation Voltage Characteristics (at T_{opr} = 0 to 60 °C(D3, D5, U3, U5), T_{opr} = -40 to 85 °C(D7, U7) / T_{opr} = -20 to 85 °C(D9, U9))

Flash Program, Erase Voltage	Flash Read Operation Voltage
V_{CC1} = 3.3 V ± 0.3 V or 5.0 V ± 0.5 V	V_{CC1}=2.7 to 5.5 V

VCC1=VCC2=5V

Timing Requirements
(VCC1 = VCC2 = 5V, VSS = 0V, at Topr = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.13　External Clock Input (XIN input) (1)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
t_c	External Clock Input Cycle Time	62.5		ns
$t_{w(H)}$	External Clock Input HIGH Pulse Width	25		ns
$t_{w(L)}$	External Clock Input LOW Pulse Width	25		ns
t_r	External Clock Rise Time		15	ns
t_f	External Clock Fall Time		15	ns

NOTES:

1. The condition is VCC1=VCC2=3.0 to 5.0V.

Table 5.14　Memory Expansion Mode and Microprocessor Mode

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{ac1(RD-DB)}$	Data Input Access Time (for setting with no wait)		(NOTE 1)	ns
$t_{ac2(RD-DB)}$	Data Input Access Time (for setting with wait)		(NOTE 2)	ns
$t_{ac3(RD-DB)}$	Data Input Access Time (when accessing multiplex bus area)		(NOTE 3)	ns
$t_{su(DB-RD)}$	Data Input Setup Time	40		ns
$t_{su(RDY-BCLK)}$	$\overline{\text{RDY}}$ Input Setup Time	30		ns
$t_{su(HOLD-BCLK)}$	$\overline{\text{HOLD}}$ Input Setup Time	40		ns
$t_{h(RD-DB)}$	Data Input Hold Time	0		ns
$t_{h(BCLK-RDY)}$	$\overline{\text{RDY}}$ Input Hold Time	0		ns
$t_{h(BCLK-HOLD)}$	$\overline{\text{HOLD}}$ Input Hold Time	0		ns

NOTES:

1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\text{x}10^9}{f(BCLK)} - 45[ns]$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{(n-0.5)\text{x}10^9}{f(BCLK)} - 45[ns]$$

n is ”2” for 1-wait setting, “3” for 2-wait setting and “4” for 3-wait setting.

3. Calculated according to the BCLK frequency as follows:

$$\frac{(n-0.5)\text{x}10^9}{f(BCLK)} - 45[ns]$$

n is “2” for 2-wait setting, “3” for 3-wait setting.

$V_{CC1}=V_{CC2}=5V$

Switching Characteristics
(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.29 Memory Expansion and Microprocessor Modes (for 2- to 3-wait setting, external area access and multiplex bus selection)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
$t_{d(BCLK-AD)}$	Address Output Delay Time	See **Figure 5.2**		25	ns
$t_{h(BCLK-AD)}$	Address Output Hold Time (in relation to BCLK)		4		ns
$t_{h(RD-AD)}$	Address Output Hold Time (in relation to RD)		(NOTE 1)		ns
$t_{h(WR-AD)}$	Address Output Hold Time (in relation to WR)		(NOTE 1)		ns
$t_{d(BCLK-CS)}$	Chip Select Output Delay Time			25	ns
$t_{h(BCLK-CS)}$	Chip Select Output Hold Time (in relation to BCLK)		4		ns
$t_{h(RD-CS)}$	Chip Select Output Hold Time (in relation to RD)		(NOTE 1)		ns
$t_{h(WR-CS)}$	Chip Select Output Hold Time (in relation to WR)		(NOTE 1)		ns
$t_{d(BCLK-RD)}$	RD Signal Output Delay Time			25	ns
$t_{h(BCLK-RD)}$	RD Signal Output Hold Time		0		ns
$t_{d(BCLK-WR)}$	WR Signal Output Delay Time			25	ns
$t_{h(BCLK-WR)}$	WR Signal Output Hold Time		0		ns
$t_{d(BCLK-DB)}$	Data Output Delay Time (in relation to BCLK)			40	ns
$t_{h(BCLK-DB)}$	Data Output Hold Time (in relation to BCLK)		4		ns
$t_{d(DB-WR)}$	Data Output Delay Time (in relation to WR)		(NOTE 2)		ns
$t_{h(WR-DB)}$	Data Output Hold Time (in relation to WR)		(NOTE 1)		ns
$t_{d(BCLK-HLDA)}$	HLDA Output Delay Time			40	ns
$t_{d(BCLK-ALE)}$	ALE Signal Output Delay Time (in relation to BCLK)			15	ns
$t_{h(BCLK-ALE)}$	ALE Signal Output Hold Time (in relation to BCLK)		–4		ns
$t_{d(AD-ALE)}$	ALE Signal Output Delay Time (in relation to Address)		(NOTE 3)		ns
$t_{h(AD-ALE)}$	ALE Signal Output Hold Time (in relation to Address)		(NOTE 4)		ns
$t_{d(AD-RD)}$	RD Signal Output Delay From the End of Address		0		ns
$t_{d(AD-WR)}$	WR Signal Output Delay From the End of Address		0		ns
$t_{dz(RD-AD)}$	Address Output Floating Start Time			8	ns

NOTES:

1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 10[ns]$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{(n-0.5)\times10^{9}}{f(BCLK)} - 40[ns]$$ n is “2” for 2-wait setting, “3” for 3-wait setting.

3. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 25[ns]$$

4. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 15[ns]$$

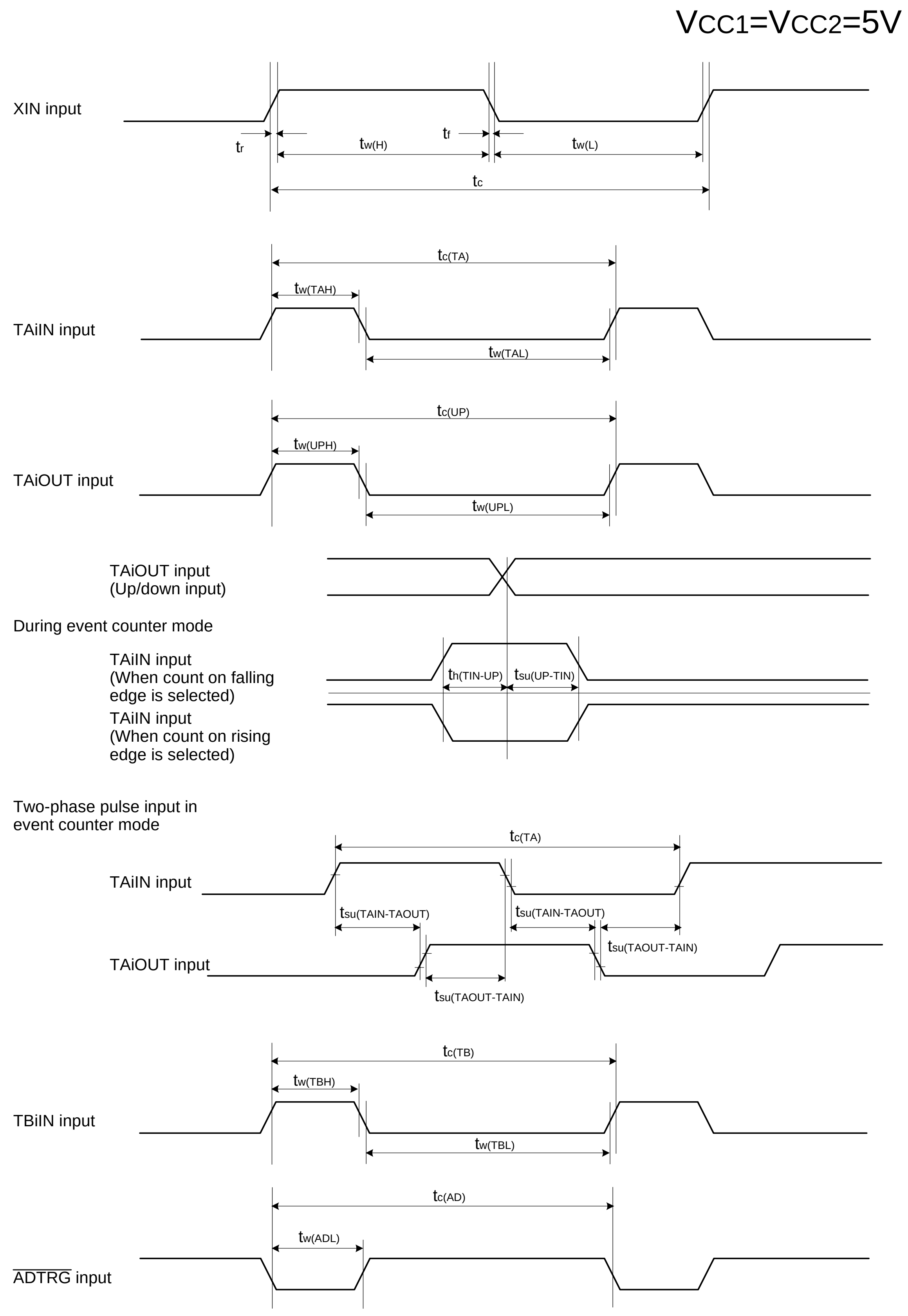


Figure 5.3 Timing Diagram (1)

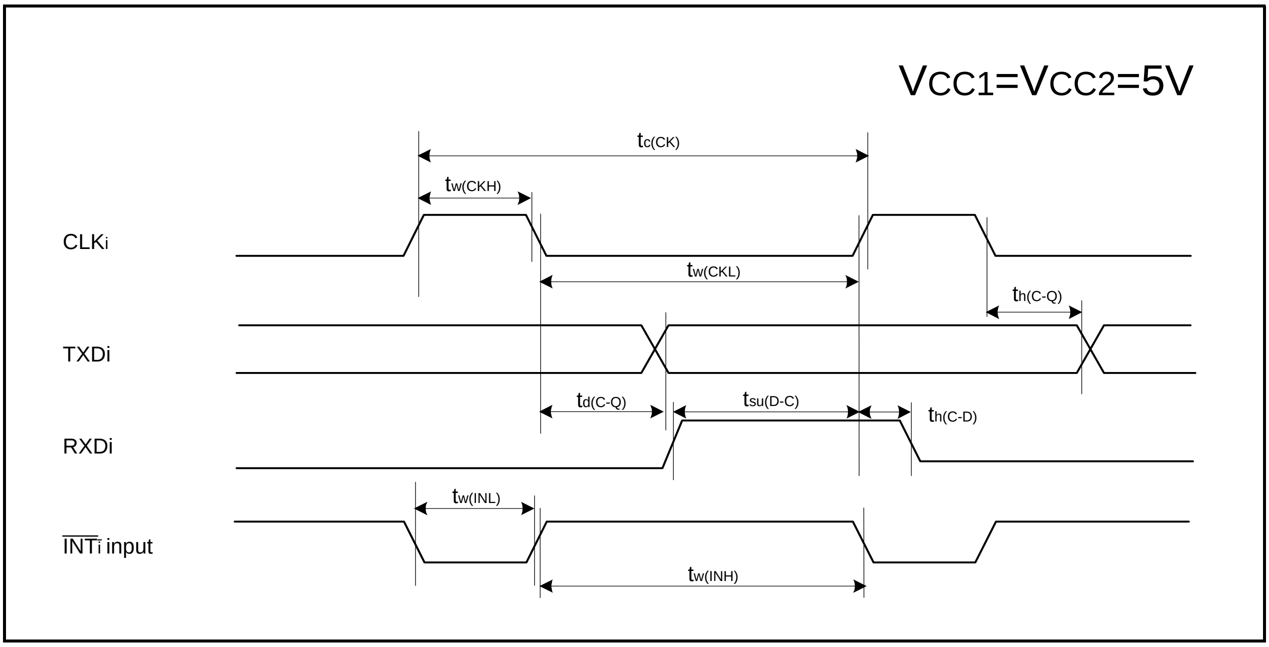
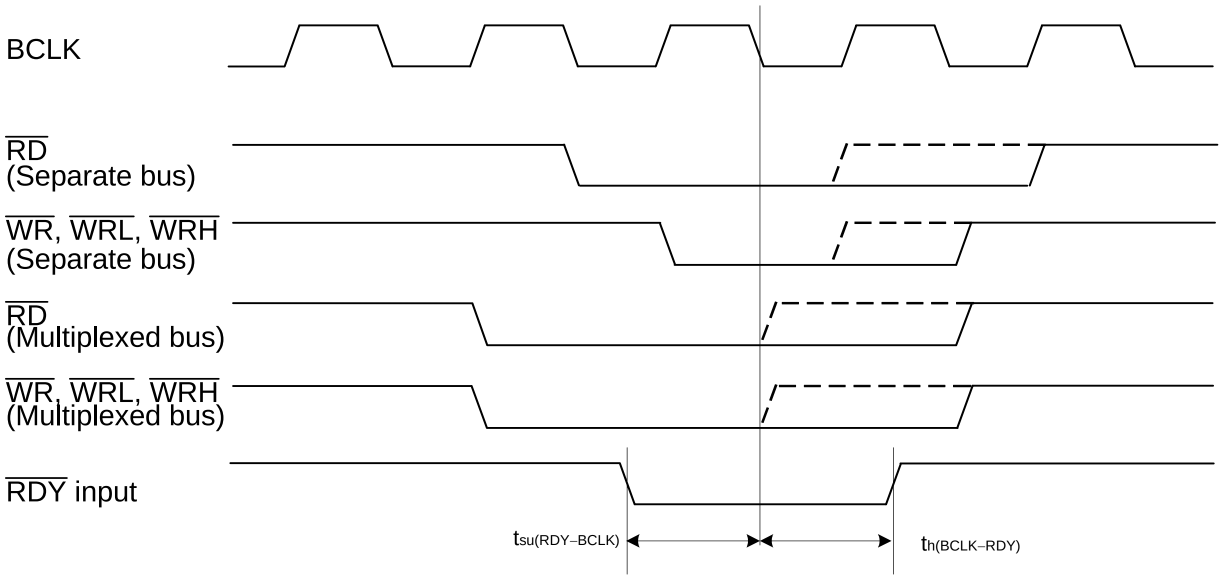


Figure 5.4 Timing Diagram (2)

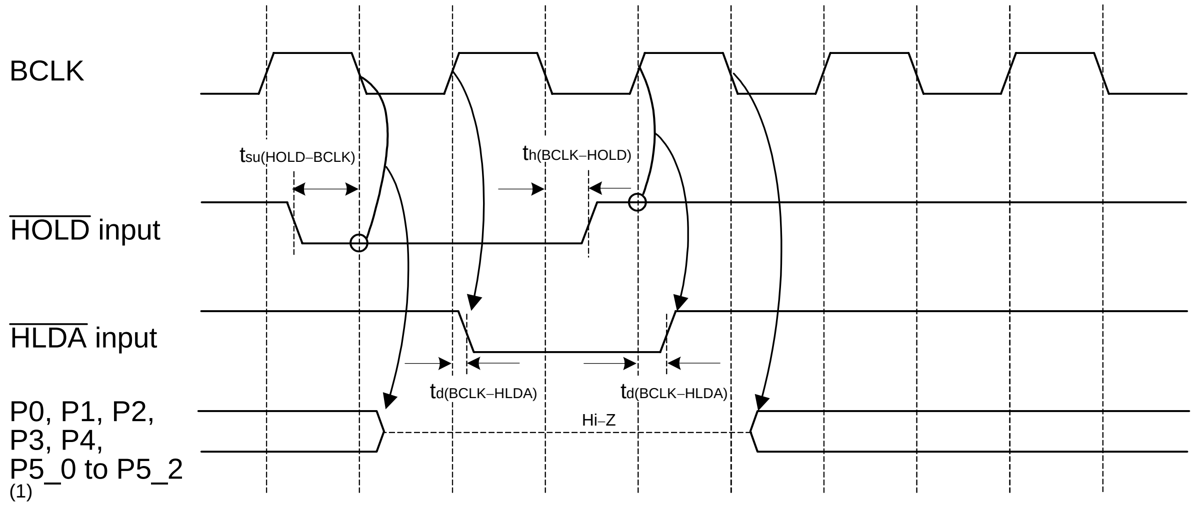
$V_{CC1}=V_{CC2}=5V$

Memory Expansion Mode, Microprocessor Mode

(Effective for setting with wait**)**



(Common to setting with wait and setting without wait**)**



NOTES:

1. These pins are set to high-impedance regardless of the input level of the BYTE pin, PM06 bit in PM0 register and PM11 bit in PM1 register.

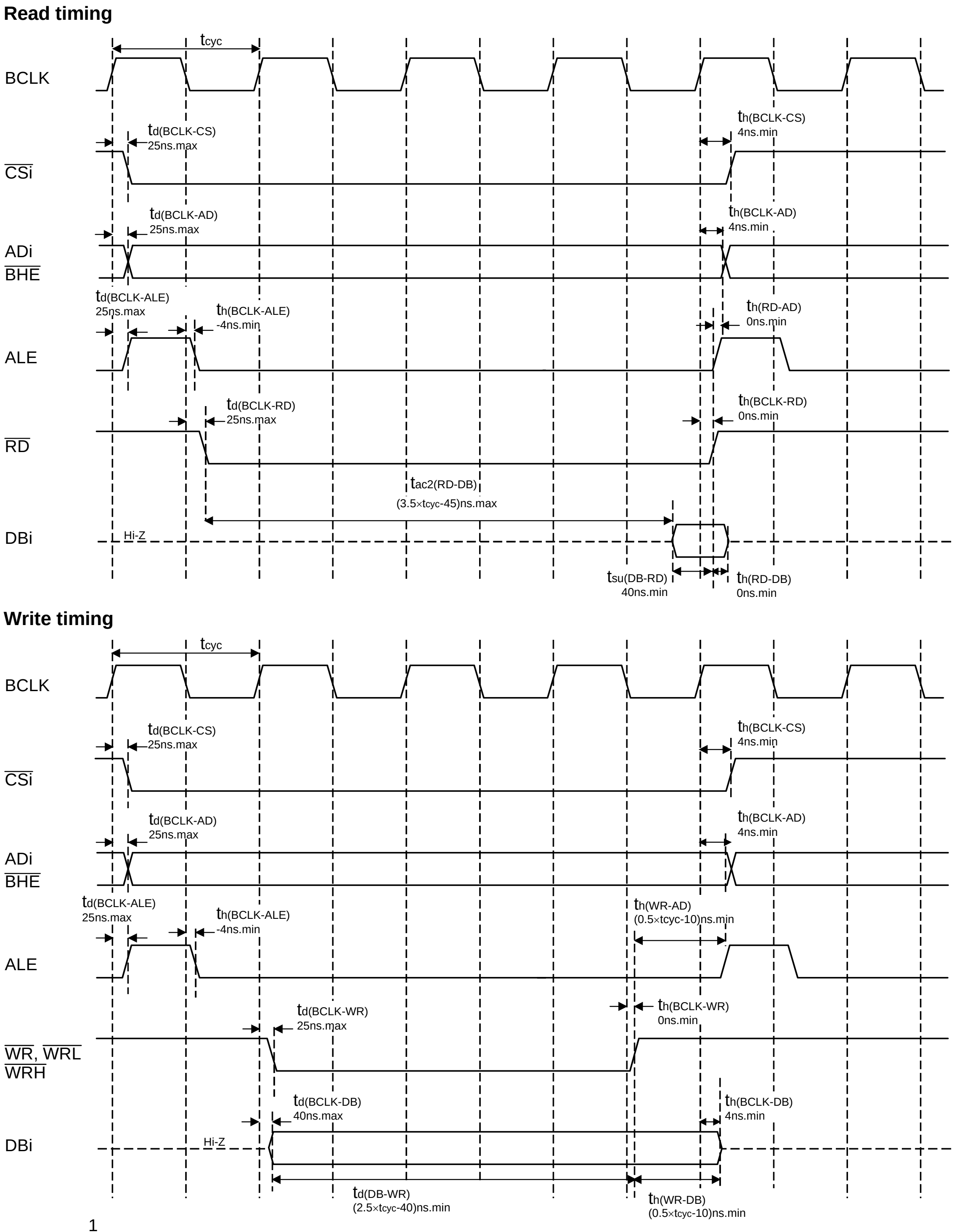
- Measuring conditions :
- $V_{CC1}=V_{CC2}=5V$
- Input timing voltage : Determined with $V_{IL}=1.0V$, $V_{IH}=4.0V$
- Output timing voltage : Determined with $V_{OL}=2.5V$, $V_{OH}=2.5V$

Figure 5.5 Timing Diagram (3)

Memory Expansion Mode, Microprocessor Mode

(for 3-wait setting and external area access**)**

$V_{CC1}=V_{CC2}=5V$



$$t_{cyc}=\frac{1}{f(BCLK)}$$

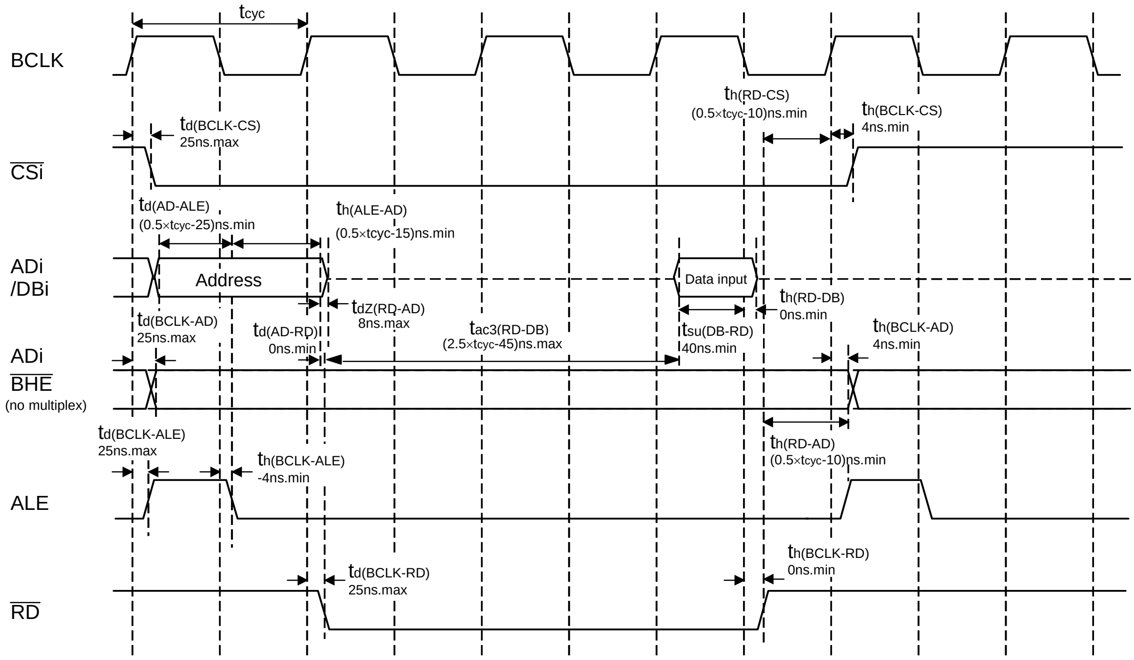
Measuring conditions
- $V_{CC1}=V_{CC2}=5V$
- Input timing voltage : $V_{IL}=0.8V$, $V_{IH}=2.0V$
- Output timing voltage : $V_{OL}=0.4V$, $V_{OH}=2.4V$

Figure 5.9 Timing Diagram (7)

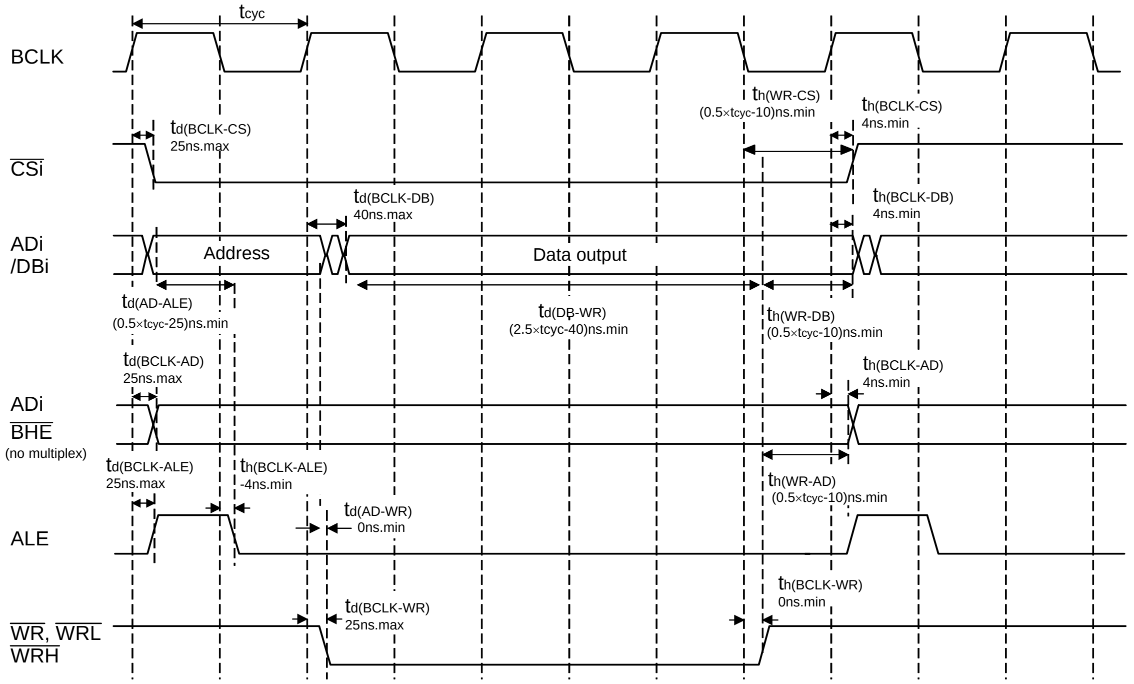
VCC1=VCC2=5V

Memory Expansion Mode, Microprocessor Mode
(For 3-wait setting, external area access and multiplex bus selection**)**

Read timing



Write timing



$$t_{cyc} = \frac{1}{f(BCLK)}$$

Measuring conditions
· VCC1=VCC2=5V
· Input timing voltage : VIL=0.8V, VIH=2.0V
· Output timing voltage : VOL=0.4V, VOH=2.4V

Figure 5.11 Timing Diagram (9)

VCC1=VCC2=3V

Switching Characteristics
(VCC1 = VCC2 = 3V, VSS = 0V, at Topr = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.46 Memory Expansion and Microprocessor Modes (for setting with no wait)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
$t_{d(BCLK-AD)}$	Address Output Delay Time	See **Figure 5.12**		30	ns
$t_{h(BCLK-AD)}$	Address Output Hold Time (in relation to BCLK)		4		ns
$t_{h(RD-AD)}$	Address Output Hold Time (in relation to RD)		0		ns
$t_{h(WR-AD)}$	Address Output Hold Time (in relation to WR)		(NOTE 2)		ns
$t_{d(BCLK-CS)}$	Chip Select Output Delay Time			30	ns
$t_{h(BCLK-CS)}$	Chip Select Output Hold Time (in relation to BCLK)		4		ns
$t_{d(BCLK-ALE)}$	ALE Signal Output Delay Time			25	ns
$t_{h(BCLK-ALE)}$	ALE Signal Output Hold Time		–4		ns
$t_{d(BCLK-RD)}$	RD Signal Output Delay Time			30	ns
$t_{h(BCLK-RD)}$	RD Signal Output Hold Time		0		ns
$t_{d(BCLK-WR)}$	WR Signal Output Delay Time			30	ns
$t_{h(BCLK-WR)}$	WR Signal Output Hold Time		0		ns
$t_{d(BCLK-DB)}$	Data Output Delay Time (in relation to BCLK)			40	ns
$t_{h(BCLK-DB)}$	Data Output Hold Time (in relation to BCLK) (3)		4		ns
$t_{d(DB-WR)}$	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns
th(WR-DB)	Data Output Hold Time (in relation to WR) (3)		(NOTE 2)		ns
$t_{d(BCLK-HLDA)}$	HLDA Output Delay Time			40	ns

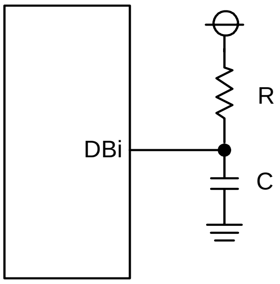
NOTES:
1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^9}{f(BCLK)} - 40[ns] \qquad f(BCLK) \text{ is 12.5MHz or less.}$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^9}{f(BCLK)} - 10[ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.
Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.
Hold time of data bus is expressed in
$t = –CR \times \ln(1–V_{OL} / V_{CC2})$
by a circuit of the right figure.
For example, when $V_{OL} = 0.2V_{CC2}$, C = 30pF, R = 1kΩ, hold time of output "L" level is
$t = –30pF \times 1k\Omega \times \ln(1–0.2V_{CC2} / V_{CC2})$
$= 6.7ns.$



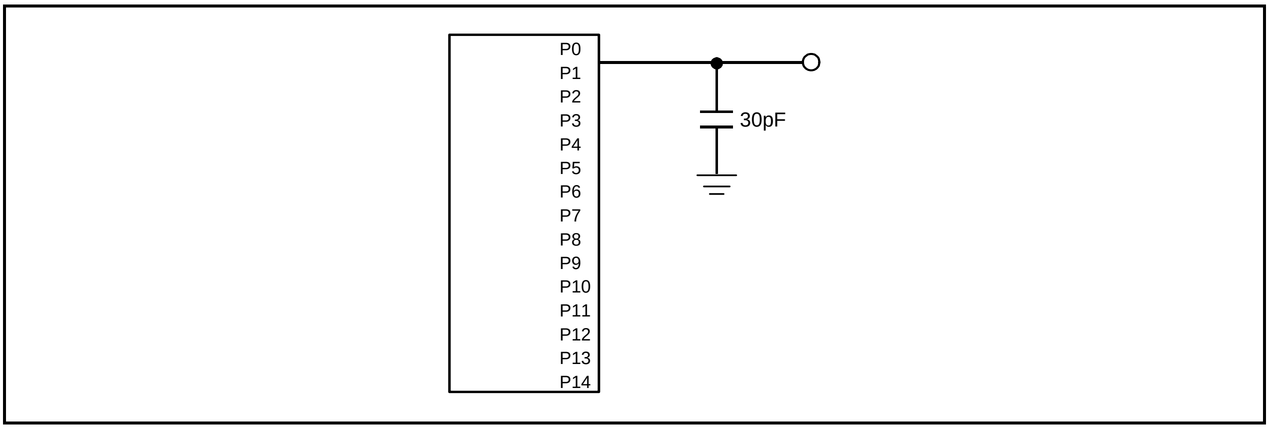


Figure 5.12 Ports P0 to P14 Measurement Circuit

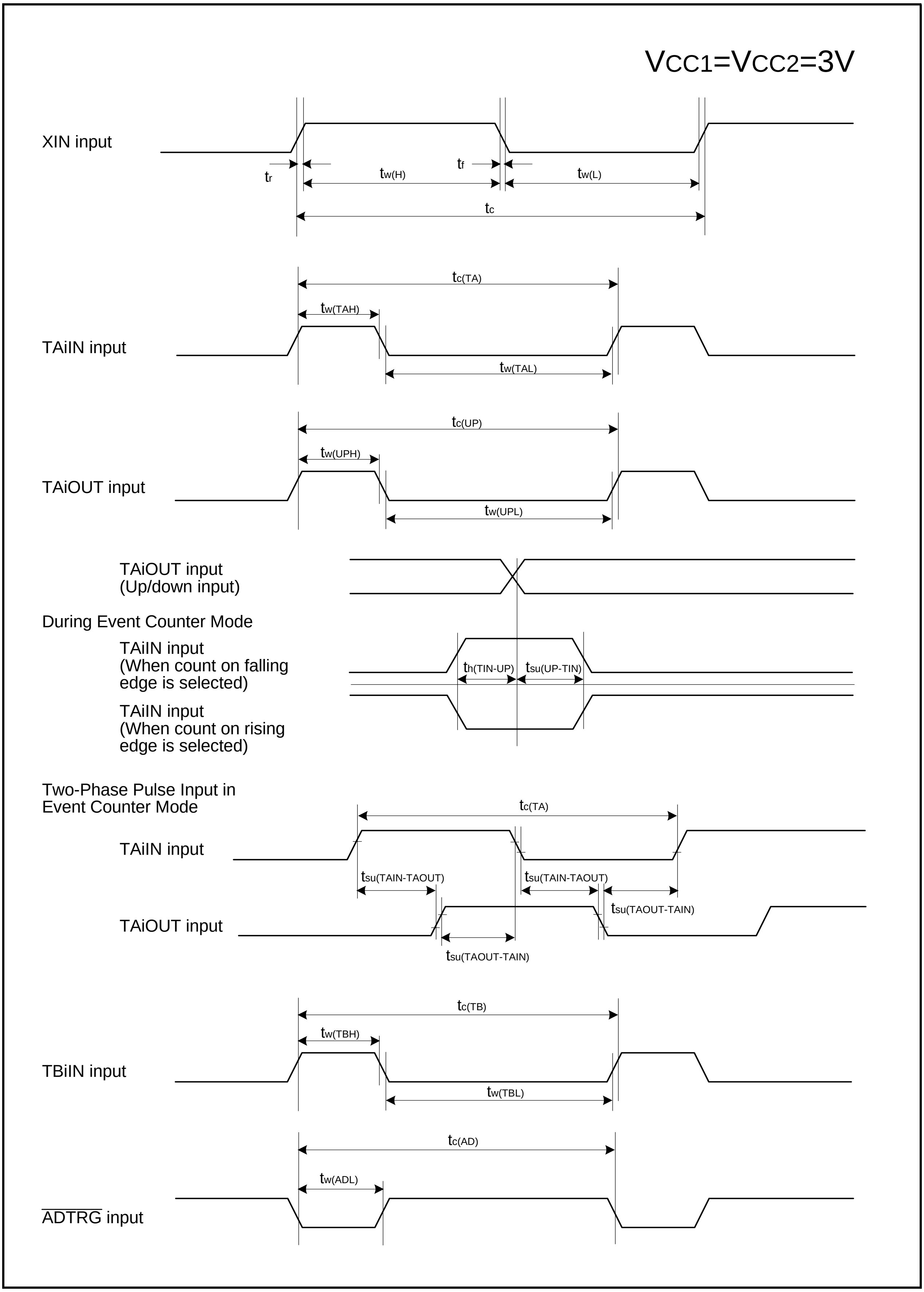
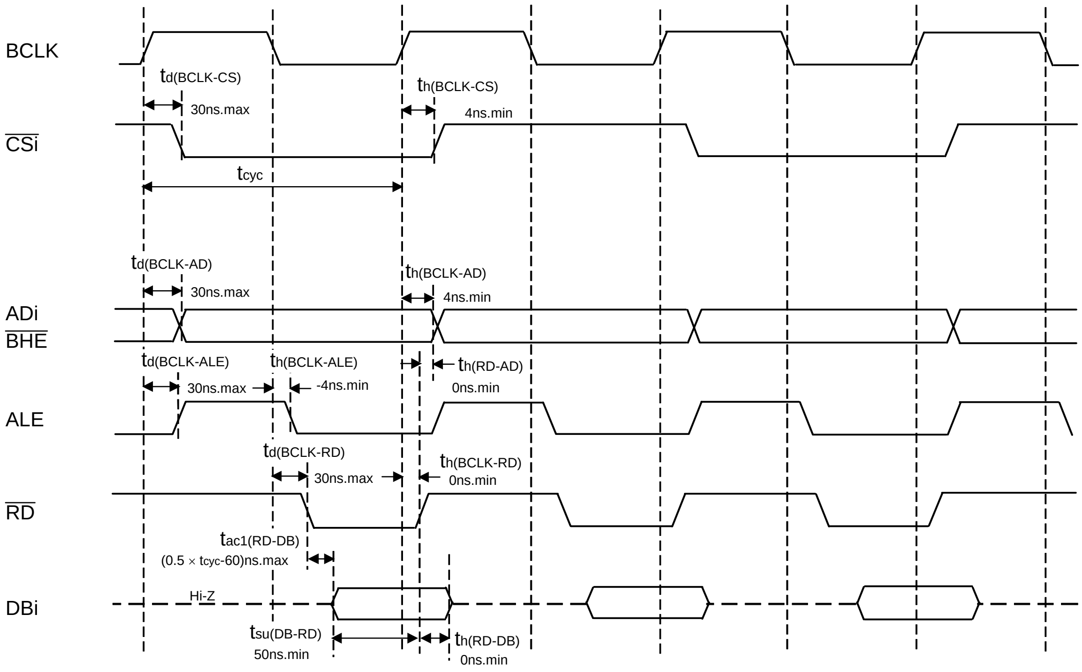


Figure 5.13 Timing Diagram (1)

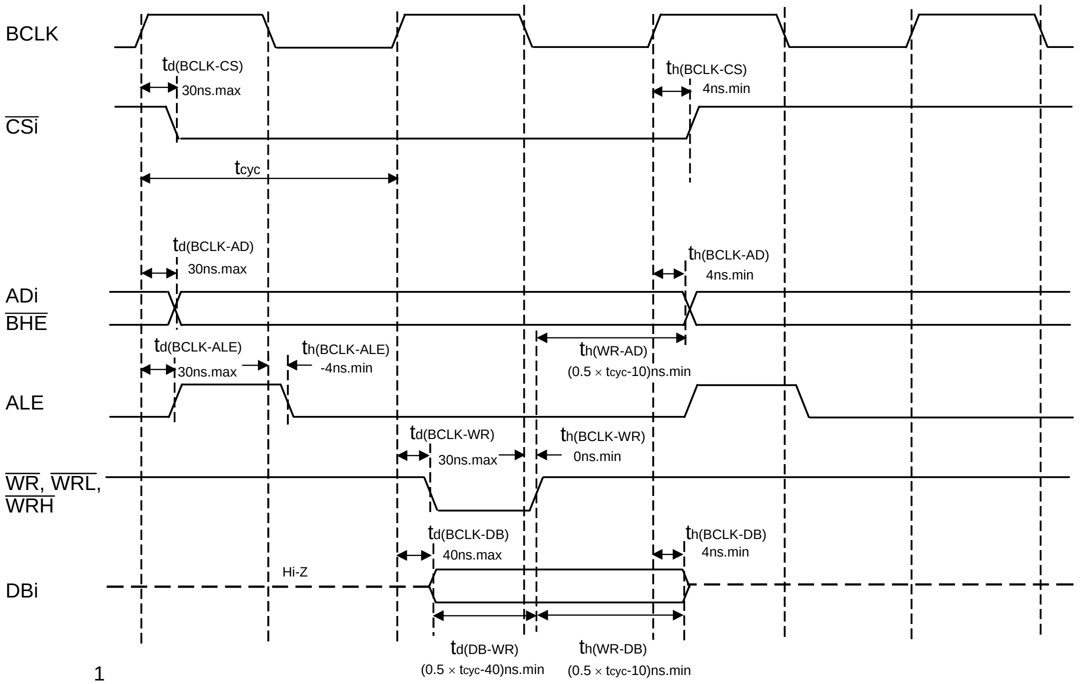
$V_{CC1}=V_{CC2}=3V$

Memory Expansion Mode, Microprocessor Mode
(for setting with no wait**)**

Read timing



Write timing



$$t_{cyc}=\frac{1}{f(BCLK)}$$

Measuring conditions
· $V_{CC1}=V_{CC2}=3V$
· Input timing voltage : $V_{IL}=0.6V$, $V_{IH}=2.4V$
· Output timing voltage : $V_{OL}=1.5V$, $V_{OH}=1.5V$

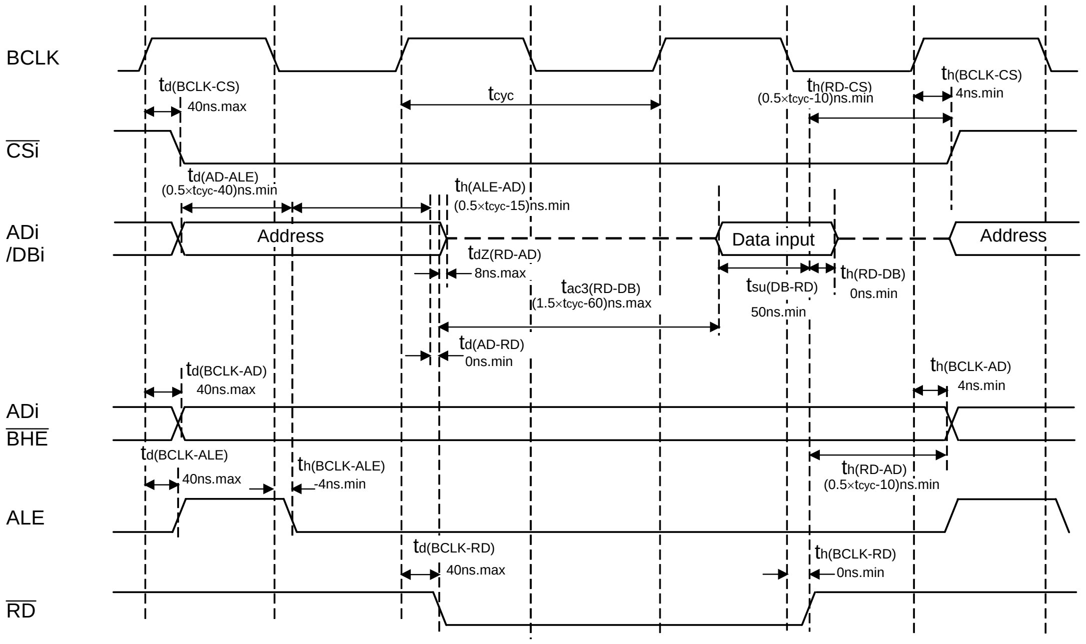
Figure 5.16 Timing Diagram (4)

Memory Expansion Mode, Microprocessor Mode

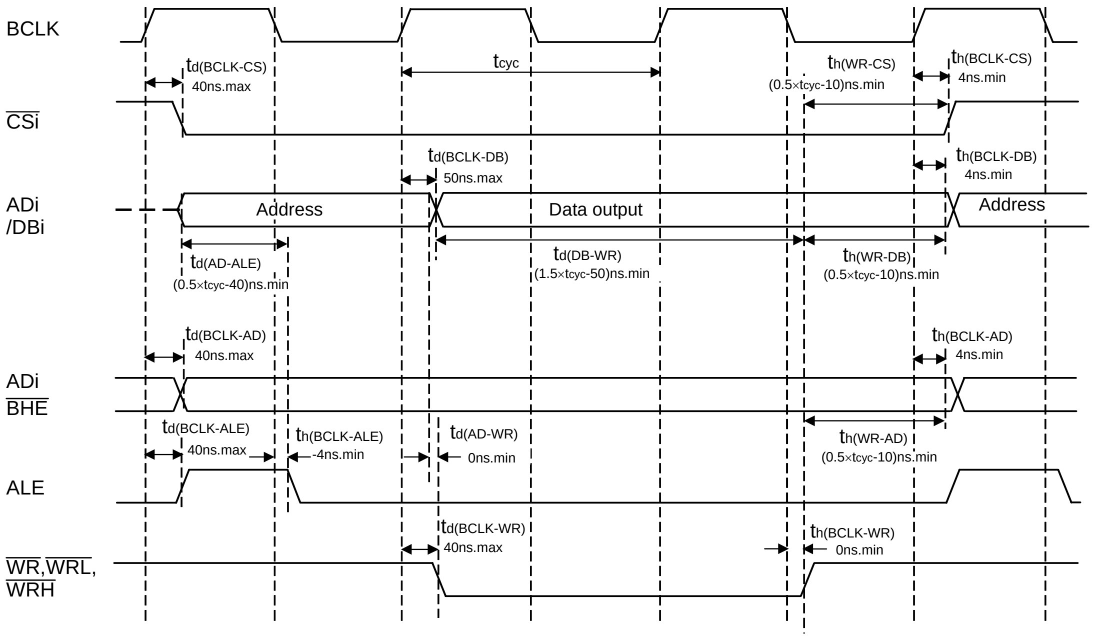
(For 2-wait setting, external area access and multiplex bus selection**)**

VCC1=VCC2=3V

Read timing



Write timing



$$t_{cyc} = \frac{1}{f(BCLK)}$$

Measuring conditions
- · VCC1=VCC2=3V
- · Input timing voltage : VIL=0.6V, VIH=2.4V
- · Output timing voltage : VOL=1.5V, VOH=1.5V

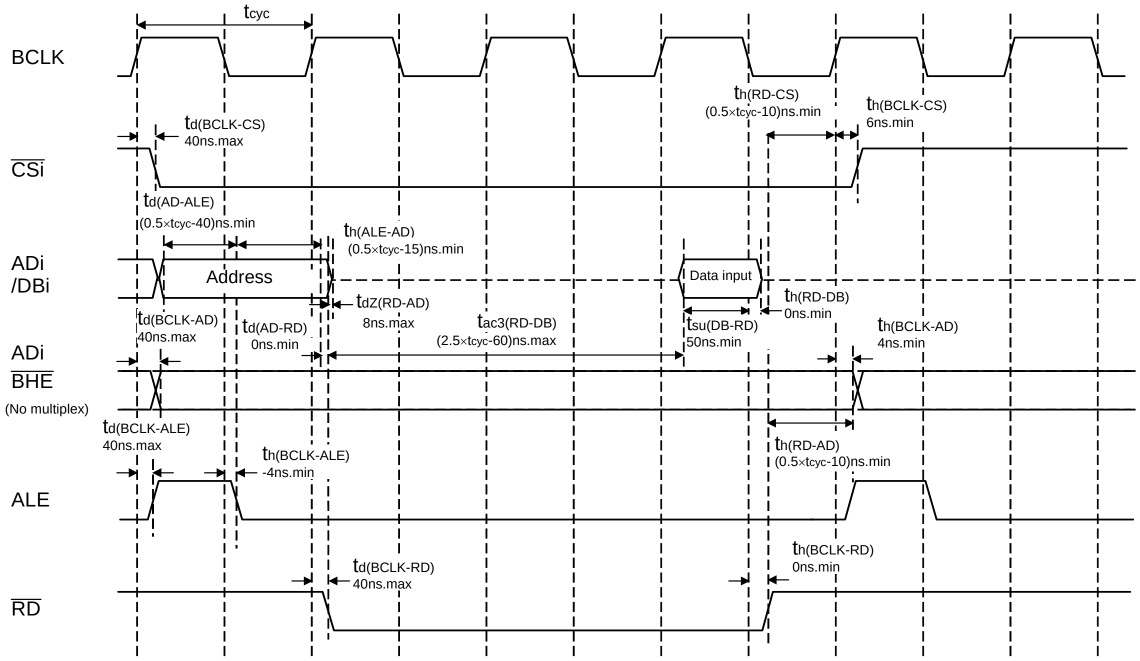
Figure 5.20 Timing Diagram (8)

$V_{CC1}=V_{CC2}=3V$

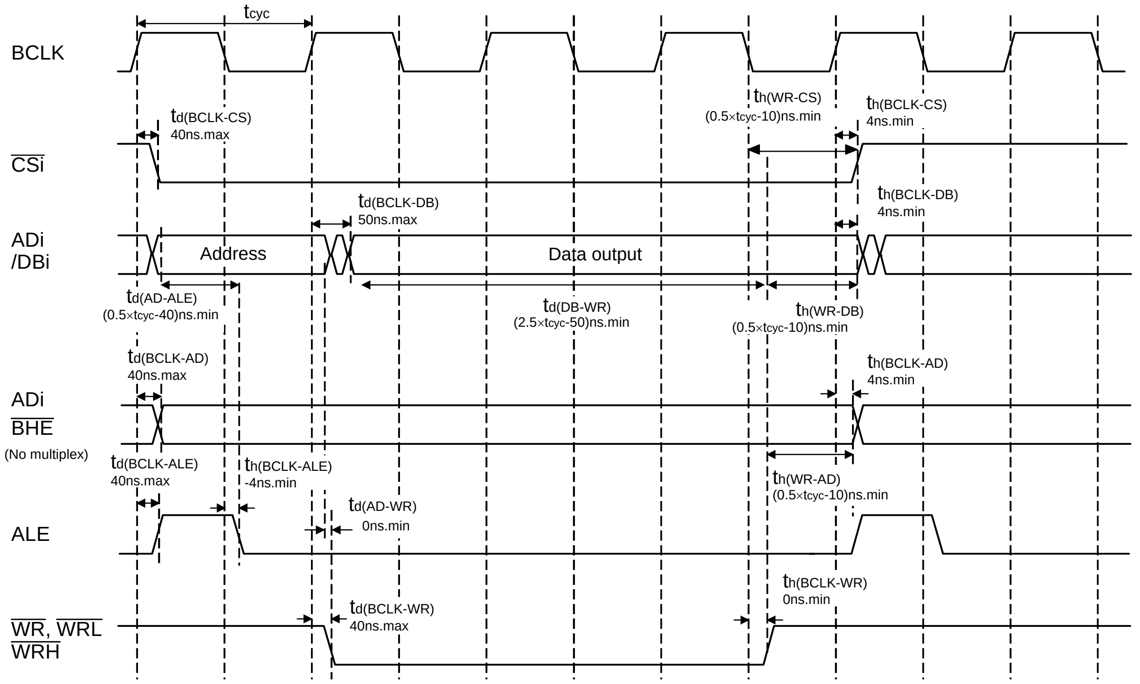
Memory Expansion Mode, Microprocessor Mode

(For 3-wait setting, external area access and multiplex bus selection)

Read timing



Write timing



$$t_{cyc}=\frac{1}{f(BCLK)}$$

Measuring conditions
- $V_{CC1}=V_{CC2}=3V$
- Input timing voltage : $V_{IL}=0.6V$, $V_{IH}=2.4V$
- Output timing voltage : $V_{OL}=1.5V$, $V_{OH}=1.5V$

Figure 5.21 Timing Diagram (9)

5.2 Electrical Characteristics (M16C/62PT)

Table 5.49 Absolute Maximum Ratings

Symbol	Parameter		Condition	Rated Value	Unit
V_{CC1}, V_{CC2}	Supply Voltage		V_{CC1}=V_{CC2}=AV_{CC}	−0.3 to 6.5	V
AV_{CC}	Analog Supply Voltage		V_{CC1}=V_{CC2}=AV_{CC}	−0.3 to 6.5	V
V_I	Input Voltage	$\overline{\text{RESET}}$, CNVSS, BYTE, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, VREF, XIN		−0.3 to V_{CC1}+0.3 (1)	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		−0.3 to V_{CC2}+0.3 (1)	V
		P7_0, P7_1		−0.3 to 6.5	V
V_O	Output Voltage	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, XOUT		−0.3 to V_{CC1}+0.3 (1)	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		−0.3 to V_{CC2}+0.3 (1)	V
		P7_0, P7_1		−0.3 to 6.5	V
P_d	Power Dissipation		$-40°C<T_{opr}\leq 85°C$	300	mW
			$85°C<T_{opr}\leq 125°C$	200	
T_{opr}	Operating Ambient Temperature	When the Microcomputer is Operating		−40 to 85 / −40 to 125 (2)	°C
		Flash Program Erase		0 to 60	
T_{stg}	Storage Temperature			−65 to 150	°C

NOTES:

1. There is no external connections for port P1_0 to P1_7, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version.
2. T version = −40 to 85 °C, V version= −40 to 125 °C.

Table 5.53 Flash Memory Version Electrical Characteristics [1] for 100 cycle products (B, U)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance [3]		100			cycle
–	Word Program Time (V_{CC1}=5.0V)			25	200	µs
–	Lock Bit Program Time			25	200	µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block	4	0.3	4	s
–		8-Kbyte block		0.3	4	s
–		32-Kbyte block		0.5	4	s
–		64-Kbyte block		0.8	4	s
–	Erase All Unlocked Blocks Time [2]				4×n	s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time [5]		20			year

Table 5.54 Flash Memory Version Electrical Characteristics [6] for 10,000 cycle products (B7, U7) (Block A and Block 1 [7])

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance [3, 8, 9]		10,000 [4]			cycle
–	Word Program Time (V_{CC1}=5.0V)			25		µs
–	Lock Bit Program Time			25		µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block	4	0.3		s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time [5]		20			year

NOTES:

1. Referenced to V_{CC1}=4.5 to 5.5V at T_{opr} = 0 to 60 °C unless otherwise specified.
2. n denotes the number of block erases.
3. Program and Erase Endurance refers to the number of times a block erase can be performed.
   If the program and erase endurance is n (n=100, 1,000, or 10,000), each block can be erased n times.
   For example, if a 4 Kbytes block A is erased after writing 1 word data 2,048 times, each to a different address, this counts as one program and erase endurance. Data cannot be written to the same address more than once without erasing the block. (Rewrite prohibited)
4. Maximum number of E/W cycles for which operation is guaranteed.
5. Ta (ambient temperature)=55 °C. As to the data hold time except Ta=55 °C, please contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor.
6. Referenced to V_{CC1} = 4.5 to 5.5V at T_{opr} = –40 to 85 °C (B7, U7 (T version)) / –40 to 125 °C (B7, U7 (V version)) unless otherwise specified.
7. Table 5.54 applies for block A or block 1 program and erase endurance > 1,000. Otherwise, use Table 5.53.
8. To reduce the number of program and erase endurance when working with systems requiring numerous rewrites, write to unused word addresses within the block instead of rewrite. Erase block only after all possible addresses are used. For example, an 8-word program can be written 256 times maximum before erase becomes necessary.
   Maintaining an equal number of erasure between block A and block 1 will also improve efficiency. It is important to track the total number of times erasure is used.
9. Should erase error occur during block erase, attempt to execute clear status register command, then block erase command at least three times until erase error disappears.
10. Set the PM17 bit in the PM1 register to “1” (wait state) when executing more than 100 times rewrites (B7 and U7).
11. Customers desiring E/W failure rate information should contact their Renesas technical support representative.

Table 5.55 Flash Memory Version Program/Erase Voltage and Read Operation Voltage Characteristics (at T_{opr} = 0 to 60 °C(B, U), Topr = –40 to 85 °C (B7, U7 (T version)) / –40 to 125 °C (B7, U7 (V version))

Flash Program, Erase Voltage	Flash Read Operation Voltage
V_{CC1} = 5.0 V ± 0.5 V	V_{CC1}=4.0 to 5.5 V